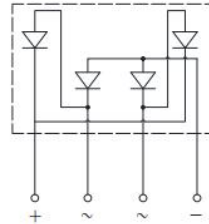


## Bridge Rectifier Diode 整流桥

### ■ Features 特点

Glass passivated chip junction 玻璃钝化结  
High surge current capability 高浪涌电流能力  
Ideal for PCB 适用于印刷电路板  
Solder dip 275°C 7S 焊接 275度 7秒内  
Package 封装: GBJ



### ■ Maximum Rating 最大额定值

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	GBJ 20005	GBJ 2001	GBJ 2002	GBJ 2004	GBJ 2006	GBJ 2008	GBJ 2010	Unit 单位
Peak Reverse Voltage 反向峰值电压	$V_{RRM}$	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	50	100	200	400	600	800	1000	V
Forward Rectified Current 正向整流电流	$I_F$	20 (With 300X300X1.6mm Heat sink 带散热)							A
Forward Rectified Current 正向整流电流	$I_F$	4.2 ( $T_c=100^{\circ}\text{C}$ Without Heat sink 不带散热)							A
Peak Surge Current 峰值浪涌电流	$I_{FSM}$	250							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	16							$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	150 $^{\circ}\text{C}$ , -55to+150 $^{\circ}\text{C}$							

### ■ Electrical Characteristics 电特性

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	$V_F$		1.05		V	$I_F=10\text{A}$
Reverse Current( $T_A=25^{\circ}\text{C}$ ) 反向电流( $T_A=125^{\circ}\text{C}$ )	$I_R$			10 500	$\mu\text{A}$	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	$C_D$		60		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

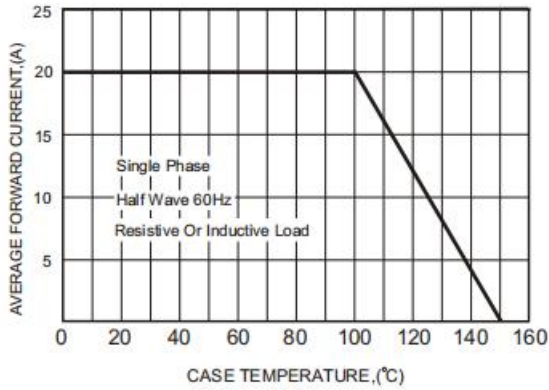


Figure 1: Forward Current Derating Curve

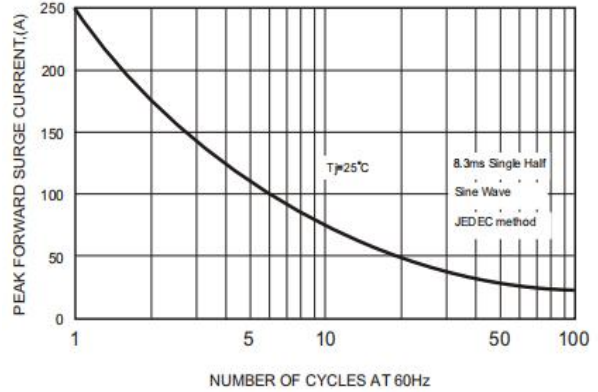


Figure 2: Peak Forward Surge Current

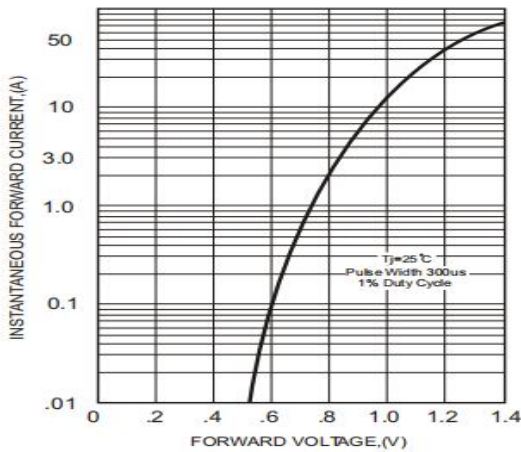


Figure 3: Instantaneous Forward Characteristics

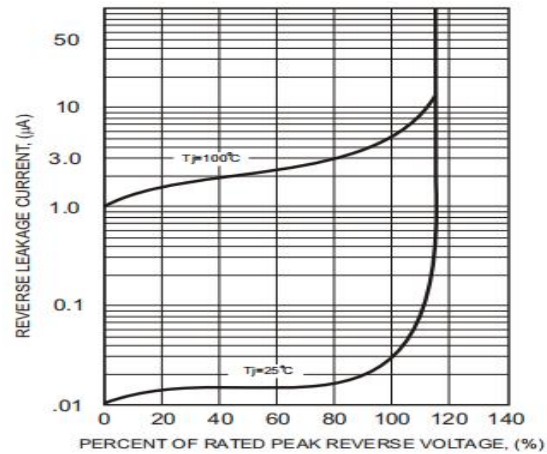


Figure 4: Reverse Leakage Characteristics

■ Dimension 外形封装尺寸

GBJ Dimensions in inches and (millimeters)

